

## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ max               | $I_D$ max<br>$T_C = +25^\circ C$ |
|------------|--------------------------------|----------------------------------|
| 80V        | 17m $\Omega$ @ $V_{GS} = 10V$  | 44A                              |
|            | 22m $\Omega$ @ $V_{GS} = 4.5V$ | 38A                              |

## Features

- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

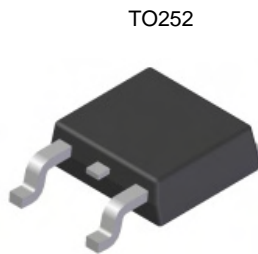
## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

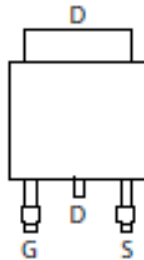
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

## Mechanical Data

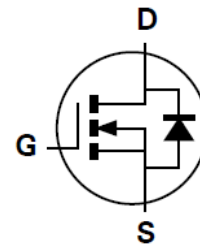
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



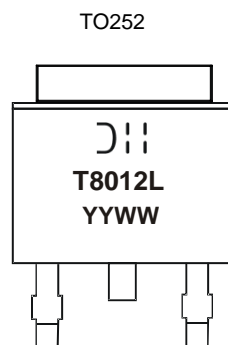
Equivalent Circuit

## Ordering Information (Note 4)

| Part Number   | Case  | Packaging         |
|---------------|-------|-------------------|
| DMT8012LK3-13 | TO252 | 2,500/Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



= Manufacturer's Marking  
 T8012L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Digit of Year (ex: 14 = 2014)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  | Symbol           | Value                   | Units |
|---|------------------|-------------------------|-------|
| Drain-Source Voltage                                    | V <sub>DSS</sub> | 80                      | V     |
| Gate-Source Voltage                                     | V <sub>GSS</sub> | ±20                     | V     |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V | I <sub>D</sub>   | T <sub>C</sub> = +25°C  | 44    |
|   |                  | T <sub>C</sub> = +100°C | 28    |
| Maximum Continuous Body Diode Forward Current (Note 5)  | I <sub>S</sub>   | 3                       | A     |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)      | I <sub>DM</sub>  | 60                      | A     |
| Avalanche Current, L=0.1mH                              | I <sub>AS</sub>  | 11.6                    | A     |
| Avalanche Energy, L=0.1mH                               | E <sub>AS</sub>  | 10.2                    | mJ    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Units |
|--|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | 2.7         | W     |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 47          | °C/W  |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | 50          | W     |
| Thermal Resistance, Junction to Case (Note 6)    | R <sub>θJC</sub>                  | 2.5         | °C/W  |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Typ   | Max  | Unit | Test Condition   |
|--|---------------------|-----|-------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 7)</b>        |                     |     |       |      |      |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 80  | -     | -    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA   |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | -   | -     | 1    | µA   | V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | -   | -     | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 7)</b>         |                     |     |       |      |      |  |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub> | 1   | -     | 3    | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA                                   |
| Static Drain-Source On-Resistance          | R <sub>DS(ON)</sub> | -   | 12    | 17   | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A  |
|  |                     | -   | 18.2  | 22   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6A  |
| Diode Forward Voltage                      | V <sub>SD</sub>     | -   | 0.9   | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 25A   |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b>    |                     |     |       |      |      |  |
| Input Capacitance                          | C <sub>iss</sub>    | -   | 1,949 | -    | pF   | V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V,<br>f = 1MHz                                     |
| Output Capacitance                         | C <sub>oss</sub>    | -   | 177   | -    |      |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    | -   | 10    | -    |      |  |
| Gate Resistance                            | R <sub>g</sub>      | -   | 0.7   | -    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz   |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Q <sub>g</sub>      | -   | 15    | -    | nC   | V <sub>DS</sub> = 40V, I <sub>D</sub> = 12A  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Q <sub>g</sub>      | -   | 34    | -    |      |  |
| Gate-Source Charge                         | Q <sub>gs</sub>     | -   | 6     | -    |      |  |
| Gate-Drain Charge                          | Q <sub>gd</sub>     | -   | 4.5   | -    |      |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | -   | 4.9   | -    | ns   | V <sub>DD</sub> = 40V, V <sub>GS</sub> = 10V,<br>I <sub>D</sub> = 12A, R <sub>G</sub> = 1.6Ω |
| Turn-On Rise Time                          | t <sub>R</sub>      | -   | 3.8   | -    |      |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> | -   | 16.5  | -    |      |  |
| Turn-Off Fall Time                         | t <sub>F</sub>      | -   | 3.5   | -    |      |  |
| Body Diode Reverse Recovery Time           | t <sub>RR</sub>     | -   | 30.2  | -    | ns   | I <sub>F</sub> = 12A, di/dt = 100A/µs  |
| Body Diode Reverse Recovery Charge         | Q <sub>rr</sub>     | -   | 34.6  | -    | nC   |  |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
  - Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

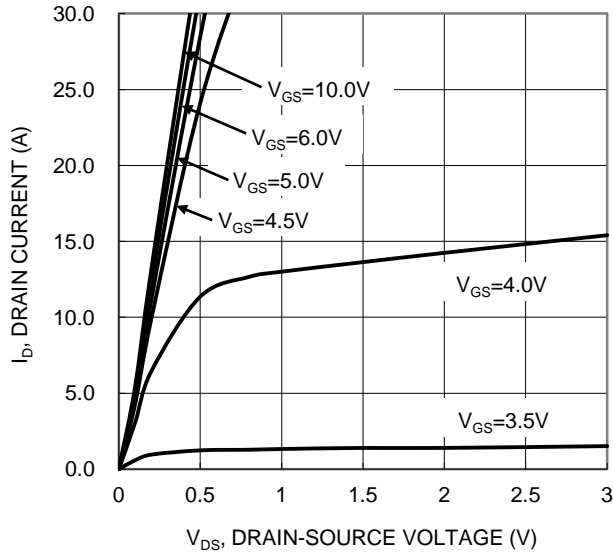


Figure 1. Typical Output Characteristic

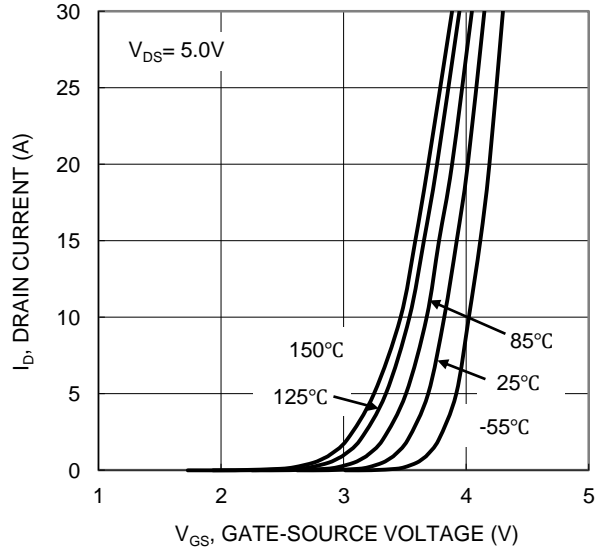


Figure 2. Typical Transfer Characteristic

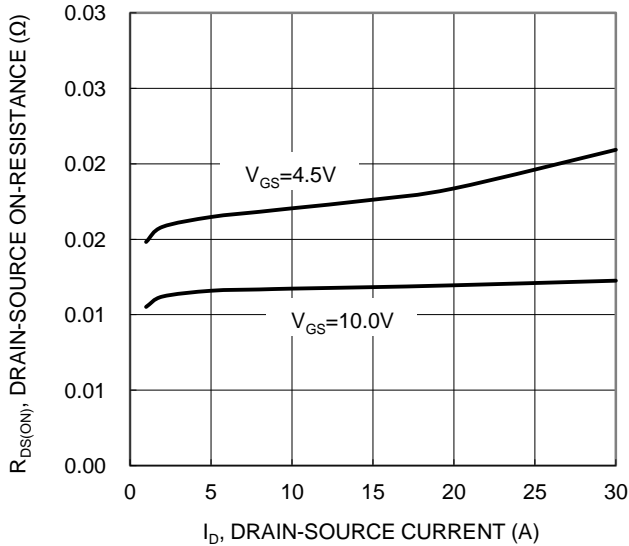


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

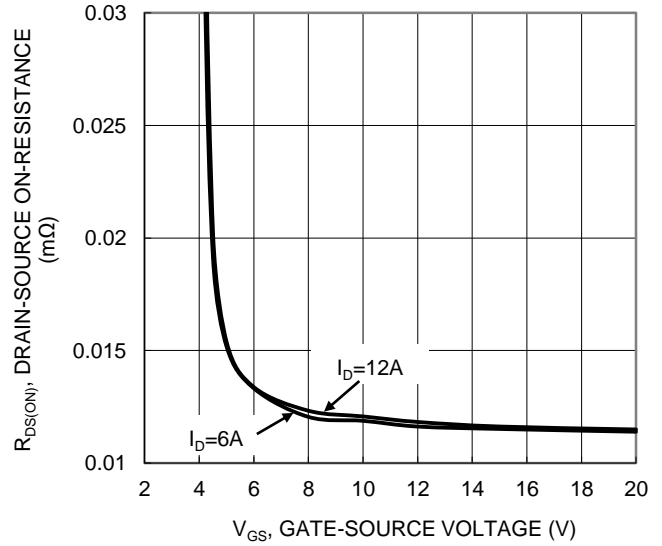


Figure 4. Typical Transfer Characteristic

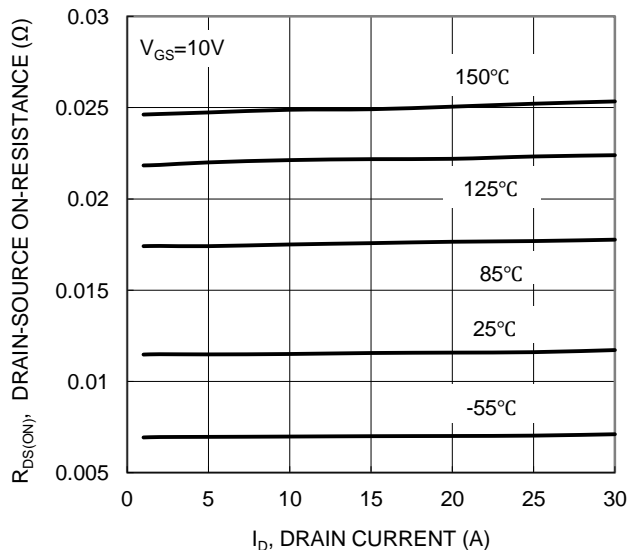


Figure 5. Typical On-Resistance vs Drain Current and Temperature

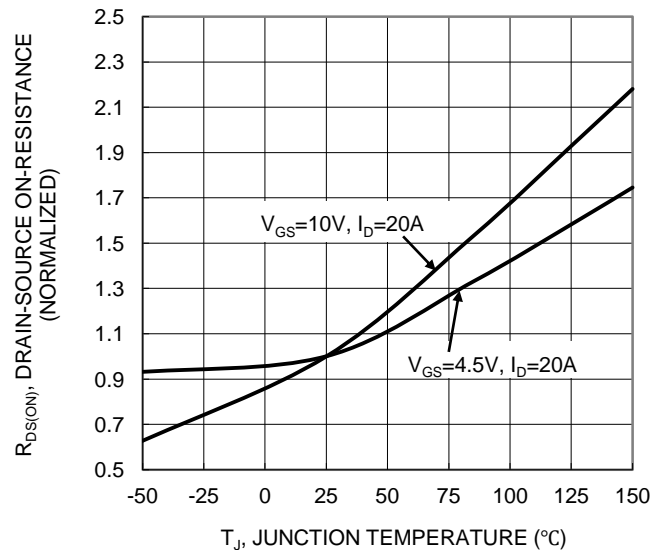


Figure 6. On-Resistance Variation with Temperature

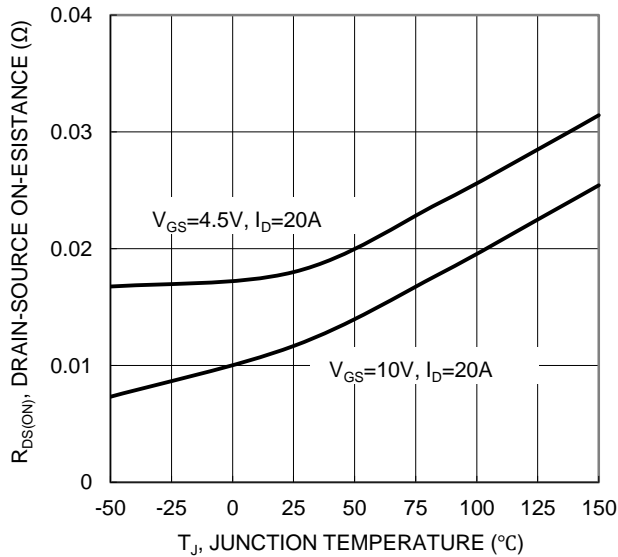


Figure 7. On-Resistance Variation with Temperature

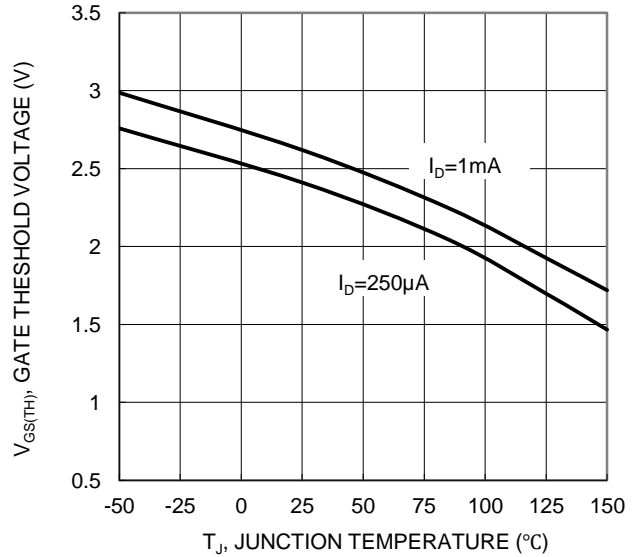


Figure 8. Gate Threshold Variation vs Temperature

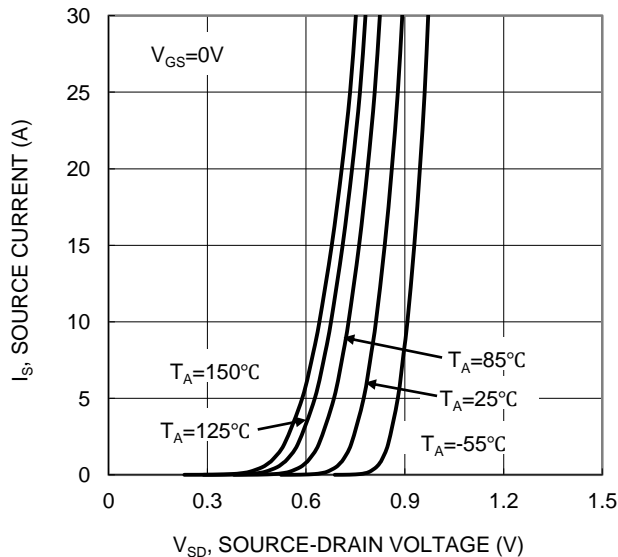


Figure 9. Diode Forward Voltage vs Current

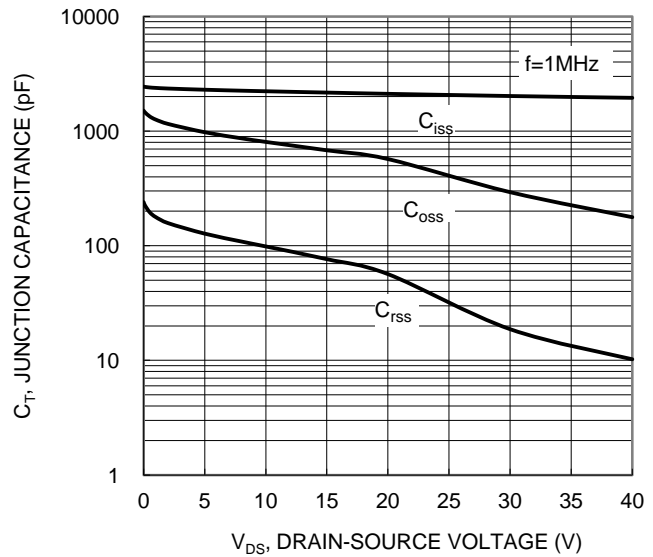


Figure 10. Typical Junction Capacitance

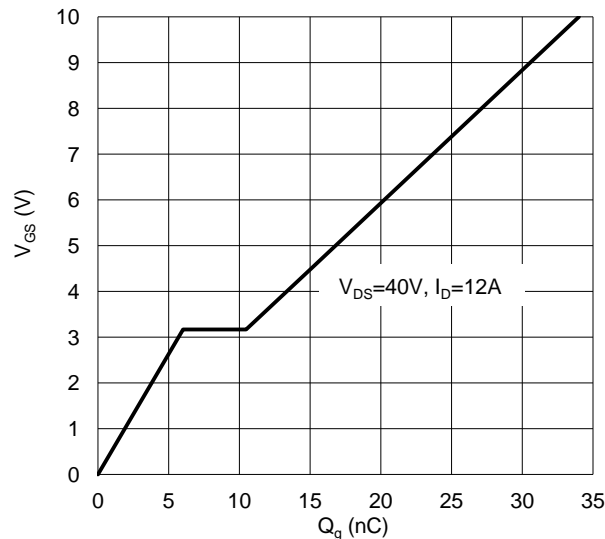


Figure 11. Gate Charge

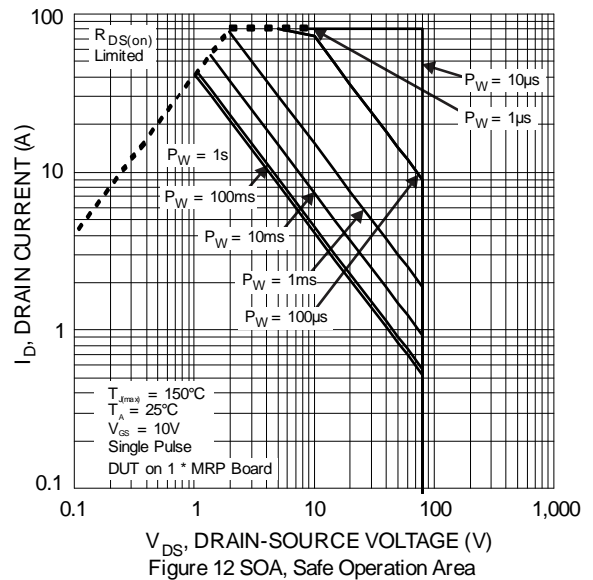


Figure 12 SOA, Safe Operation Area

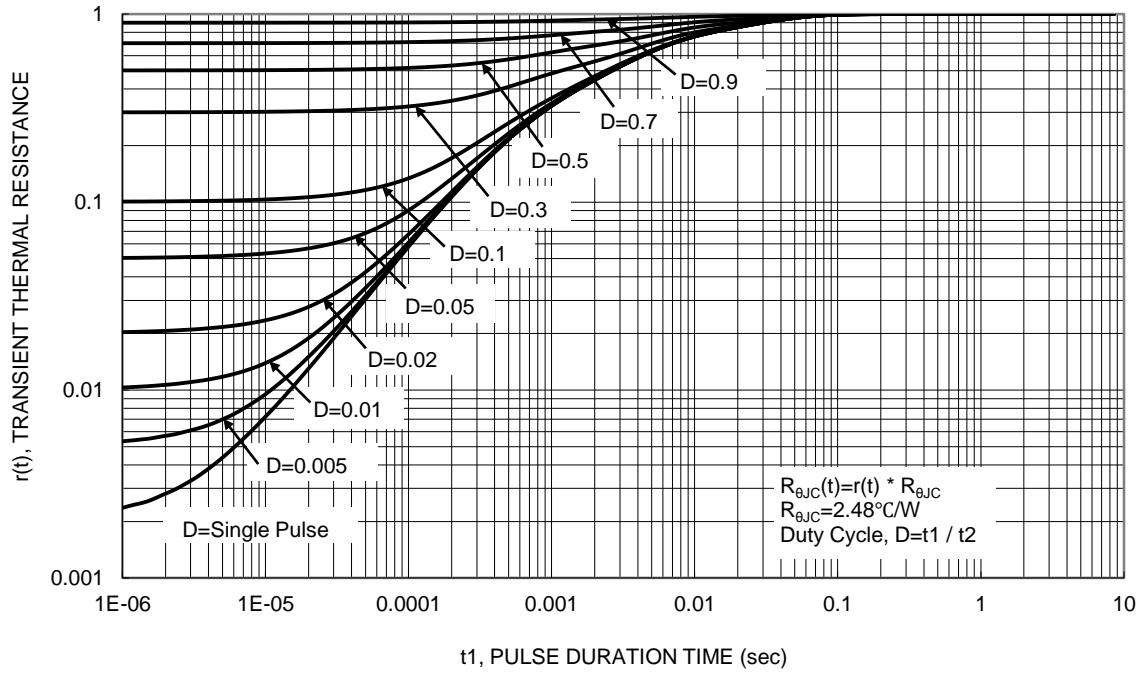
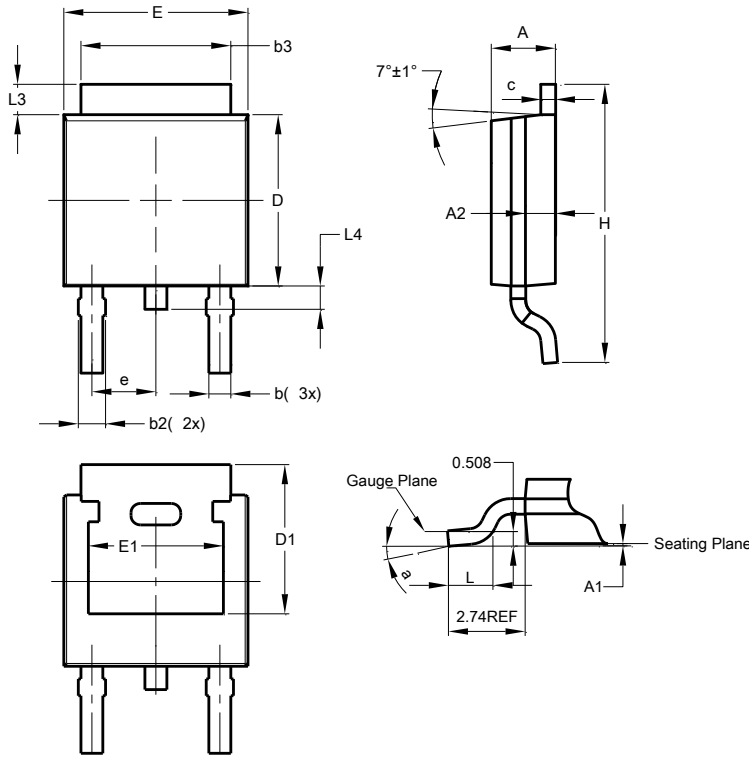


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

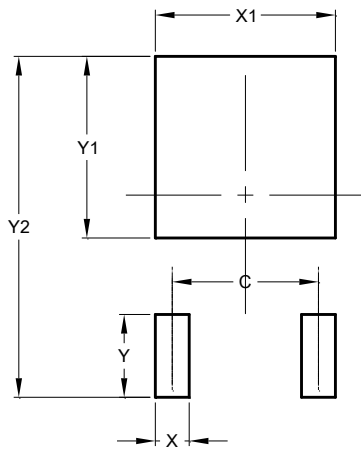
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| TO252 (DPAK)         |      |       |       |
|----------------------|------|-------|-------|
| Dim                  | Min  | Max   | Typ   |
| A                    | 2.19 | 2.39  | 2.29  |
| A1                   | 0.00 | 0.13  | 0.08  |
| A2                   | 0.97 | 1.17  | 1.07  |
| b                    | 0.64 | 0.88  | 0.783 |
| b2                   | 0.76 | 1.14  | 0.95  |
| b3                   | 5.21 | 5.46  | 5.33  |
| c                    | 0.45 | 0.58  | 0.531 |
| D                    | 6.00 | 6.20  | 6.10  |
| D1                   | 5.21 | -     | -     |
| e                    | -    | -     | 2.286 |
| E                    | 6.45 | 6.70  | 6.58  |
| E1                   | 4.32 | -     | -     |
| H                    | 9.40 | 10.41 | 9.91  |
| L                    | 1.40 | 1.78  | 1.59  |
| L3                   | 0.88 | 1.27  | 1.08  |
| L4                   | 0.64 | 1.02  | 0.83  |
| a                    | 0°   | 10°   | -     |
| All Dimensions in mm |      |       |       |

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 4.572         |
| X          | 1.060         |
| X1         | 5.632         |
| Y          | 2.600         |
| Y1         | 5.700         |
| Y2         | 10.700        |

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